DISCRETE SEMICONDUCTORS

DATA SHEET

PEMB1; PUMB1 PNP/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = 22 kΩ

Product specification Supersedes data of 2001 Sep 13 2003 Oct 15





 $k\Omega$

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMB1; PUMB1

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
TR1	PNP	_	_	_
TR2	PNP	_	_	_
R1	hias resistor	22	_	kO

22

QUICK REFERENCE DATA

bias resistor

DESCRIPTION

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	(AGE	MARKING CODE	NPN/PNP	NPN/NPN
TIPE NUMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMB1	SOT666	_	Z4	PEMD2	PEMH1
PUMB1	SOT363	SC-88	B*3 ⁽¹⁾	PUMD2	PUMH1

R2

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
I TPE NUMBER	SIMIPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION	
PEMB1	6 5 4	1	emitter TR1	
PUMB1	6 5 4	2	base TR1	
	R1 R2	3	collector TR2	
	TR2	4	emitter TR2	
	TR1	5	base TR2	
	$\left[\begin{array}{c c} & & & \\ & & & \end{array}\right]$ R2 $\left[\begin{array}{c c} R1 & & \\ & & \end{array}\right]$	6	collector TR1	
	1 2 3			
	1 2 3 Top view MAM477			
	. 55			

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PEMB1; PUMB1

ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
I TPE NOWIBER	NAME	DESCRIPTION	VERSION
PEMB1	_	plastic surface mounted package; 6 leads	SOT666
PUMB1	_	plastic surface mounted package; 6 leads	SOT363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT				
Per transistor									
V _{CBO}	collector-base voltage	open emitter	_	-50	V				
V _{CEO}	collector-emitter voltage	open base	_	-50	V				
V _{EBO}	emitter-base voltage	open collector	_	-10	V				
VI	input voltage								
	positive		_	+10	V				
	negative		_	-40	V				
Io	output current (DC)		_	-100	mA				
I _{CM}	peak collector current		_	-100	mA				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C							
	SOT363	note 1	_	200	mW				
	SOT666	notes 1 and 2	_	200	mW				
T _{stg}	storage temperature		-65	+150	°C				
Tj	junction temperature		_	150	°C				
T _{amb}	operating ambient temperature		-65	+150	°C				
Per device	•	·	·	•					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C							
	SOT363	note 1	_	300	mW				
	SOT666	notes 1 and 2	_	300	mW				

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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PEMB1; PUMB1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0$	_	_	-180	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	60	_	_	
V _{CEsat}	saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
V _{i(off)}	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-1.1	-0.8	V
V _{i(on)}	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-2.5	-1.7	_	V
R1	input resistor		15.4	22	28.6	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

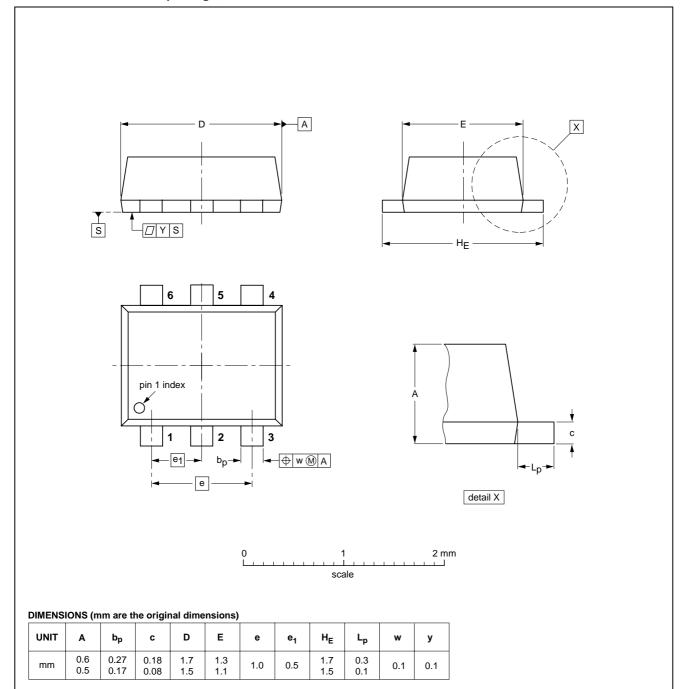
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PEMB1; PUMB1

PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



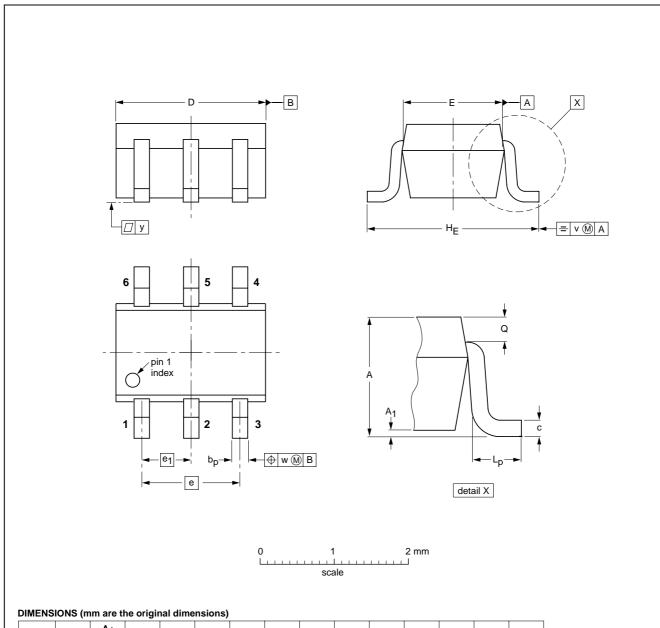
OUTLINE		REFERENCES EUROPEAN				
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMB1; PUMB1

Plastic surface mounted package; 6 leads

SOT363



UN	IIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	٧	w	у
m	m	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

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Printed in The Netherlands

R75/02/pp8

Date of release: 2003 Oct 15

Document order number: 9397 750 11789

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